

# **isc** Silicon PNP Power Transistor

# 2SB1607

#### DESCRIPTION

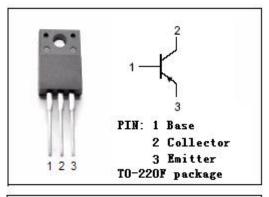
- Large Collector Current
- Satisfactory Linearity of Foward Current Transfer Ratio
- Low Collector to Emitter Saturation Voltage
  - : V<sub>CE(sat)</sub>= -0.5V(Max.)@I<sub>C</sub>= -5A
- Full-pack Package With Outstanding Insulation,
  Which Can Be Installed to The Heat Sink With One Screw
- Complement to Type 2SD2469
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

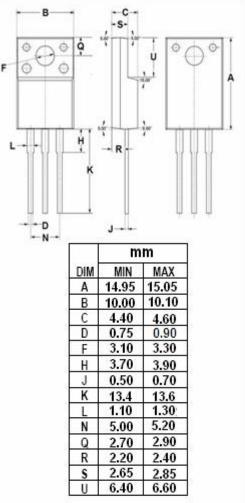
### APPLICATIONS

• Designed for power switching and general purpose applications.

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-130	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-80	V
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V
lc	Collector Current-Continuous	-7	А
Ісм	Collector Current-Peak	-15	А
	Collector Power Dissipation @ Ta=25°C	2	W
Pc	Collector Power Dissipation @ $T_C=25^{\circ}C$	40	W
TJ	Junction Temperature 150		°C
T <sub>stg</sub>	Storage Temperature Range	- <b>55~150</b> °C	

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)





isc website: www.iscsemi.cn

1



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### **ELECTRICAL CHARACTERISTICS**

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.25A			-0.5	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.25A			-1.5	V
І <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-50	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= -0.1A; Vce= -2V	45			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -2V	90		260	
f⊤	Current-Gain—Bandwidth Product	I <sub>E</sub> = 0.5A; V <sub>CE</sub> = -10V;f=10MHz		30		MHz

Switching Times

ton	Turn-on Time		0.5	μ <b>S</b>
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = -3A; I <sub>B1</sub> = -I <sub>B2</sub> = -0.3A,	1.5	μ <b>S</b>
t <sub>f</sub>	Fall Time		0.1	μs

2

#### • h<sub>FE-2</sub> Classifications

Q	Р
90-180	130-260



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3